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電源管理



顯示驅動



二三極管



LDO穩壓器



觸摸芯片



MOS管



運算放大器



存儲芯片



MCU



串口通信

20N03H

產品規格說明書

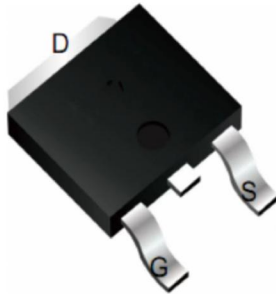
20N03H 30V N-Channel Enhancement Mode MOSFET



Description

The 20N03-TD uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a battery protection or in other Switching application.

TO-252-2L Pin Configuration

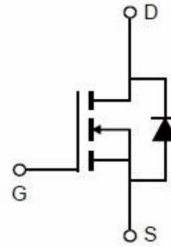


General Features

$V_{DS} = 30V$ $I_D = 20A$
 $R_{DS(ON)} < 20m\Omega$ @ $V_{GS}=10V$

Application

Battery protection
 Load switch
 Uninterruptible power supply



Package Marking and Ordering Information

Product ID	Package	Marking	QTY(PCS)	Packing method
20N03-TD	TO-252-2L	20N03-TD	2500	Reel

Absolute Maximum Ratings ($T_c=25^\circ C$ unless otherwise specified)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_c=25^\circ C$	Continuous Drain Current, V_{GS} @ 10V ¹	20	A
$I_D@T_c=100^\circ C$	Continuous Drain Current, V_{GS} @ 10V ¹	15	A
$I_D@T_A=25^\circ C$	Continuous Drain Current, V_{GS} @ 10V ¹	7.3	A
$I_D@T_A=70^\circ C$	Continuous Drain Current, V_{GS} @ 10V ¹	5.8	A
I_{DM}	Pulsed Drain Current ²	50	A
EAS	Single Pulse Avalanche Energy ³	8.1	mJ
I_{AS}	Avalanche Current	12.7	A
$P_D@T_c=25^\circ C$	Total Power Dissipation ⁴	20.8	W
$P_D@T_A=25^\circ C$	Total Power Dissipation ⁴	2	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	6	$^\circ C/W$

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Electrical Characteristics (T_J=25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	30	---	---	V
ΔBV _{DSS} /ΔT _J	BVDSS Temperature Coefficient	Reference to 25°C, I _D =1mA	---	0.023	---	V/°C
R _{DS(on)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =10A	---	17	20	mΩ
		V _{GS} =4.5V, I _D =8A	---	20	25	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.0	1.2	2.5	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	-4.2	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =24V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =24V, V _{GS} =0V, T _J =55°C	---	---	5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =10A	---	5.5	---	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	2.3	---	Ω
Q _g	Total Gate Charge (4.5V)	V _{DS} =15V, V _{GS} =4.5V, I _D =10A	---	4.9	---	nC
Q _{gs}	Gate-Source Charge		---	1.66	---	
Q _{gd}	Gate-Drain Charge		---	1.85	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =15V, V _{GS} =10V, R _G =3.3, I _D =10A	---	1.6	---	ns
T _r	Rise Time		---	15.8	---	
T _{d(off)}	Turn-Off Delay Time		---	13	---	
T _f	Fall Time		---	4.8	---	
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	---	416	---	pF
C _{oss}	Output Capacitance		---	62	---	
C _{rss}	Reverse Transfer Capacitance		---	51	---	
I _S	Continuous Source Current ^{1,5}	V _G =V _D =0V, Force Current	---	---	24	A
I _{SM}	Pulsed Source Current ^{2,5}		---	---	50	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1.2	V
t _{rr}	Reverse Recovery Time	I _F =10A, dI/dt=100A/μs, T _J =25°C	---	8.7	---	nS
Q _{rr}	Reverse Recovery Charge		---	1.95	---	nC

Note :

1.The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.

2The data tested by pulsed , pulse width .The EAS data shows Max. rating .

3he test condition is V_{GS}≤300us , duty cycle $\frac{t_{on}}{t_{on}+t_{off}} \leq 0.5$, V_{GS}=10V, L=0.1mH, I_{AS}=12.7A

4.The power dissipation is limited by 150°C junction temperature

5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

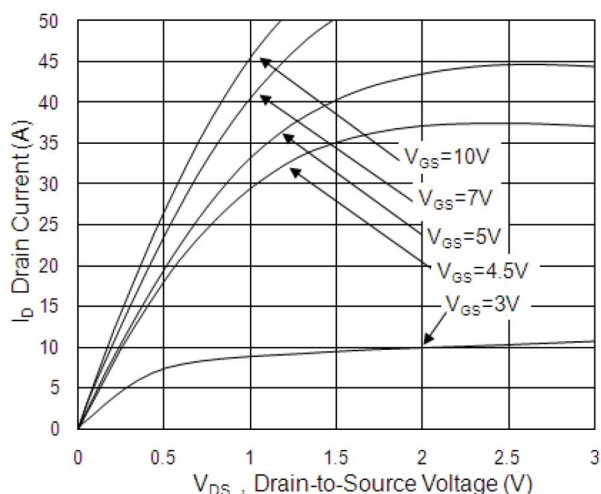


Fig.1 Typical Output Characteristics

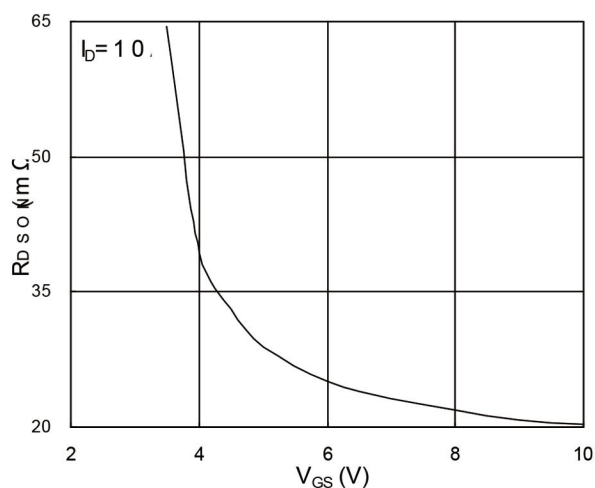


Fig.2 On-Resistance vs. Gate-Source

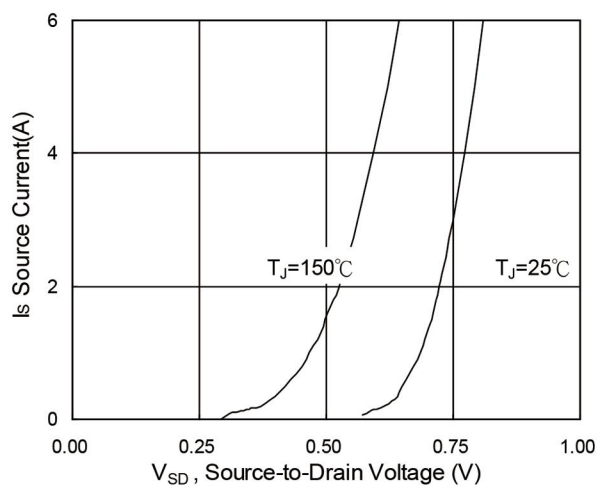


Fig.3 Forward Characteristics Of Reverse

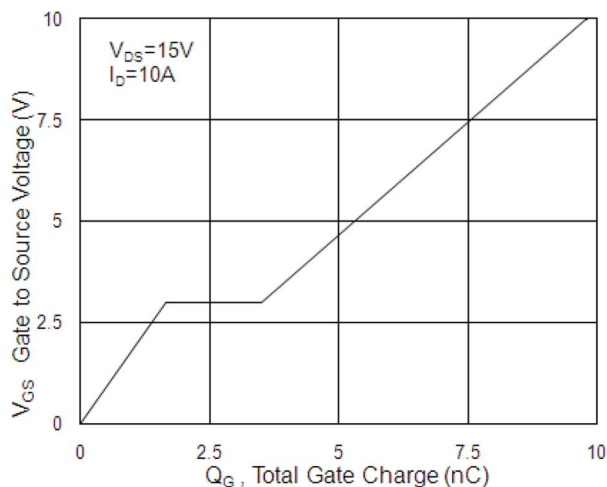


Fig.4 Gate-Charge Characteristics

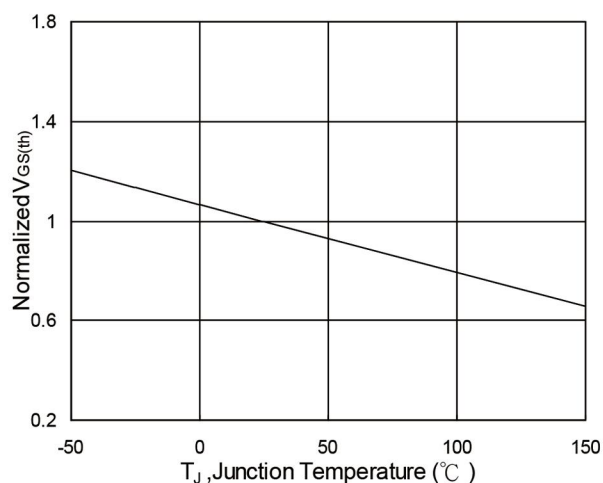


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

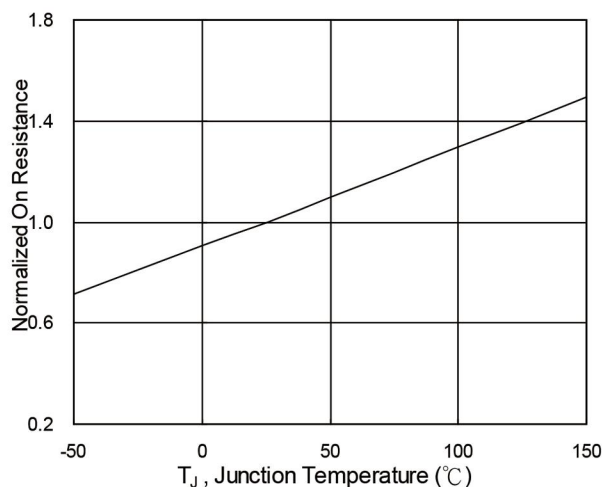


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

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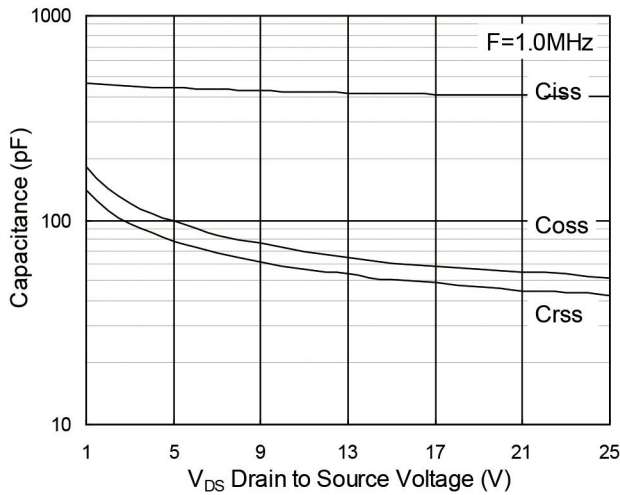


Fig.7 Capacitance

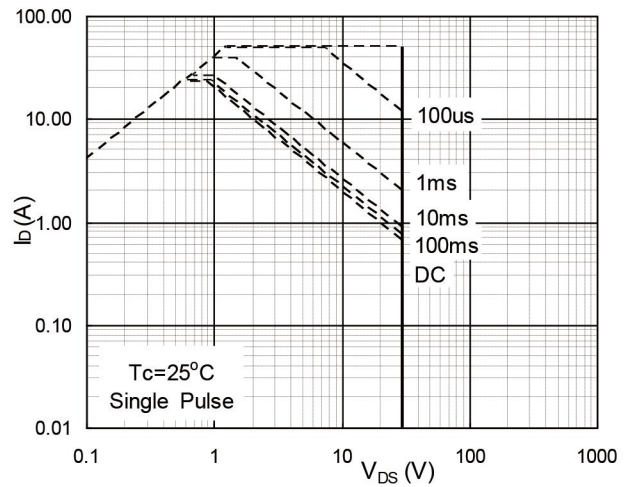


Fig.8 Safe Operating Area

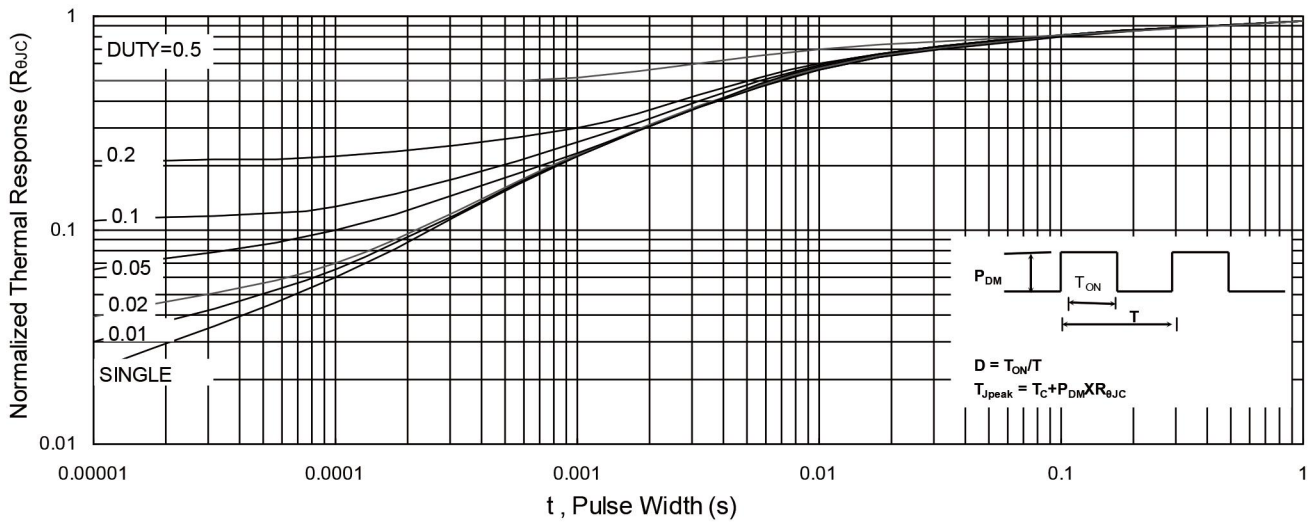


Fig.9 Normalized Maximum Transient Thermal Impedance

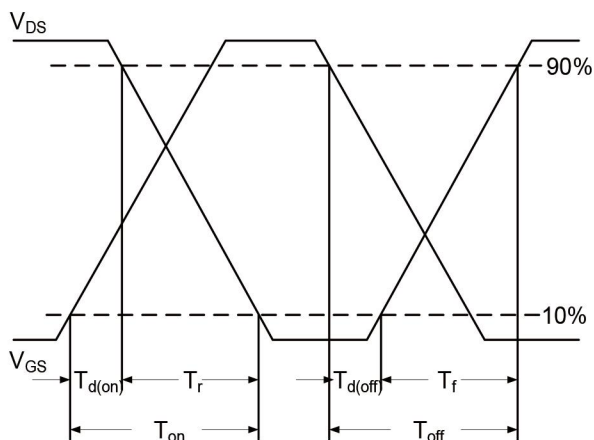


Fig.10 Switching Time Waveform

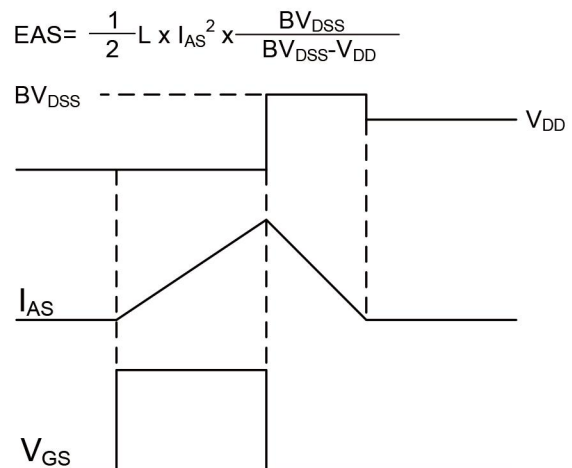
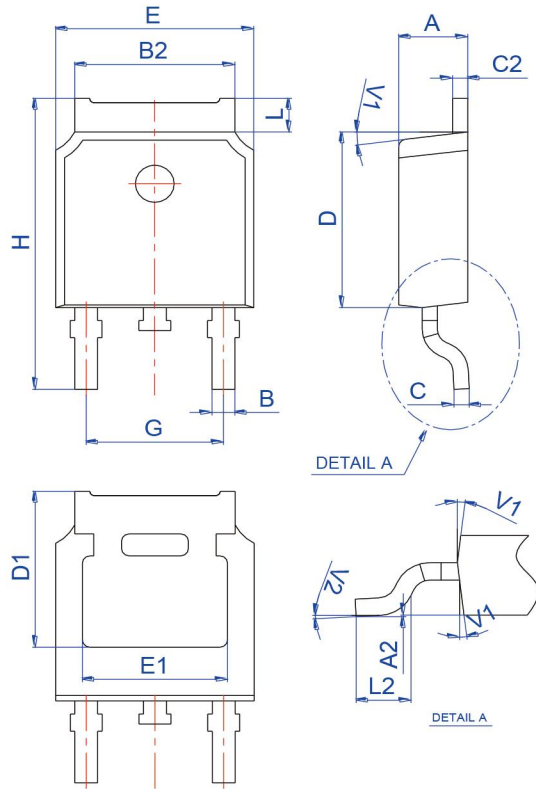


Fig.11 Unclamped Inductive Switching Waveform

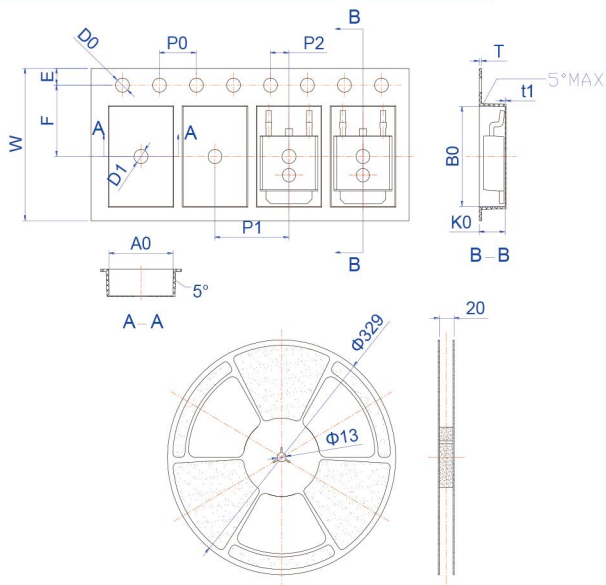
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Package Mechanical Data



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Reel Specification-TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583